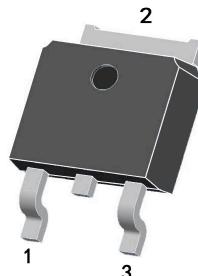


-40V P-Channel Mosfet**FEATURES**

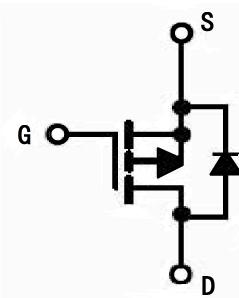
- $R_{DS(ON)} \leq 9.2\text{m}\Omega$ (7.1mΩ Typ.) @ $V_{GS}=-10\text{V}$
- $R_{DS(ON)} \leq 13\text{m}\Omega$ (9.3mΩ Typ.) @ $V_{GS}=-4.5\text{V}$
- AEC Q101 qualified
- Green Product (RoHS compliant)

TO-252-2L

1. GATE
2. DRAIN
3. SOURCE

APPLICATIONS

- Automotive Systems
- PWM Applications
- Load Switch
- Power Management

P-CHANNEL MOSFET**MARKING**

YYMM: Date Code(year &month)

XX: Internal Code

MAXIMUM RATINGS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	-40	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current @ $V_{GS}=-10\text{V}$ note1	$T_c = 25^\circ\text{C}$	A
		$T_c = 100^\circ\text{C}$	A
I_{DM}	Pulsed Drain Current note2	-280	A
E_{AS}	Single Pulsed Avalanche Energy note3	182	mJ
P_D	Power Dissipation $T_c = 25^\circ\text{C}$	88	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.7	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS T_c=25 °C unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -40V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note4	V _{GS} = -10V, I _D = -30A	-	7.1	9.2	mΩ
		V _{GS} = -4.5V, I _D = -20A	-	9.3	13	
Dynamic Characteristics note5						
C _{iss}	Input Capacitance	V _{DS} = -20V, V _{GS} =0V, f=1.0MHz	-	7202	-	pF
C _{oss}	Output Capacitance		-	626	-	pF
C _{rss}	Reverse Transfer Capacitance		-	438	-	pF
Q _g	Total Gate Charge	V _{DS} = -20V, I _D = -20A, V _{GS} = -10V	-	116	-	nC
Q _{gs}	Gate-Source Charge		-	23	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	21	-	nC
Switching Characteristics note5						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -20V, I _D = -20A, V _{GS} = -10V, R _{GEN} =3Ω	-	15.2	-	ns
t _r	Turn-on Rise Time		-	89	-	ns
t _{d(off)}	Turn-off Delay Time		-	123	-	ns
t _f	Turn-off Fall Time		-	102	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -30A	-	-	-1.2	V
trr	Reverse Recovery Time	V _{GS} =0V, I _S = -20A, di/dt=100A/μs	-	25	-	ns
Qrr	Reverse Recovery Charge		-	17	-	nC

Notes:1. T_c=25°C Limited only by maximum temperature allowed. Calculated continuous current based on maximum allowable junction temperature.

2. PW≤10μs, Duty cycle≤1%
- 3 . EAS condition:TJ= 25°C , VDD= -20V, VG= -10V, L= 0.5mH, RG= 25Ω, IAS= -27A
- 4 . Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
- 5 . Guaranteed by design, not subject to production testing

TYPICAL PERFORMANCE CHARACTERISTICS

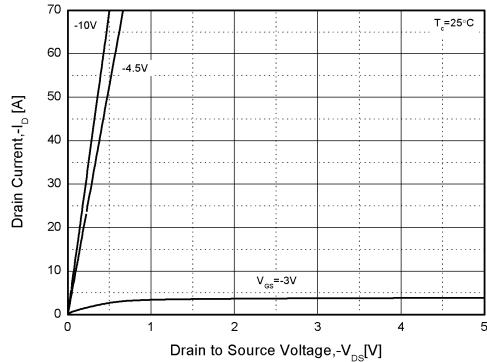


Figure1. Output Characteristics

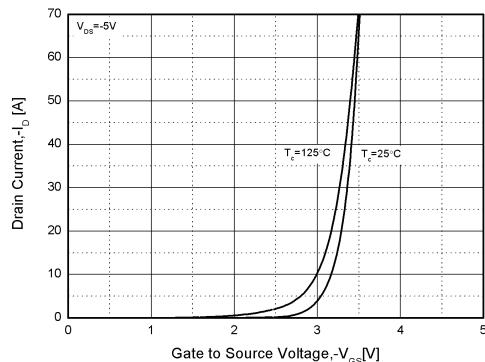


Figure2. Transfer Characteristics

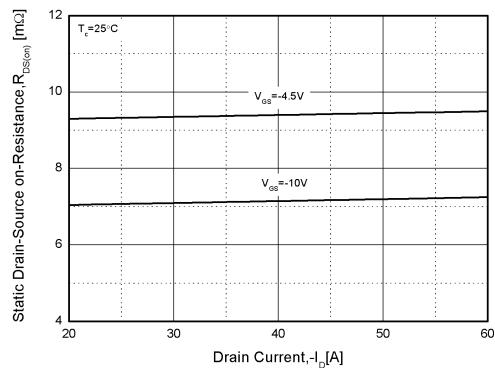


Figure3. R_{DSON} -Drain Current

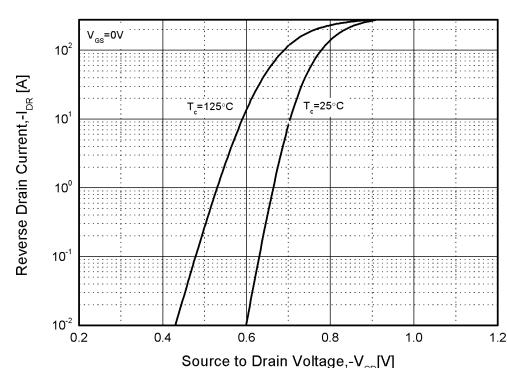


Figure4. Typical Source-Drain Diode Forward Voltage

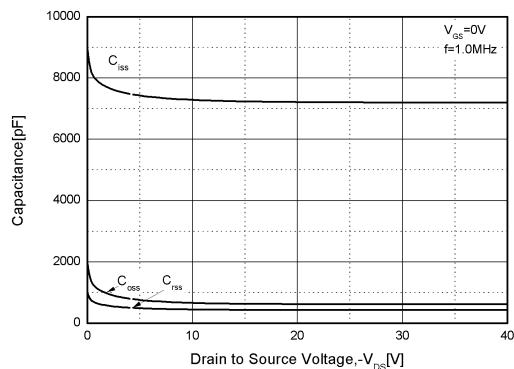


Figure5. Capacitance Characteristics

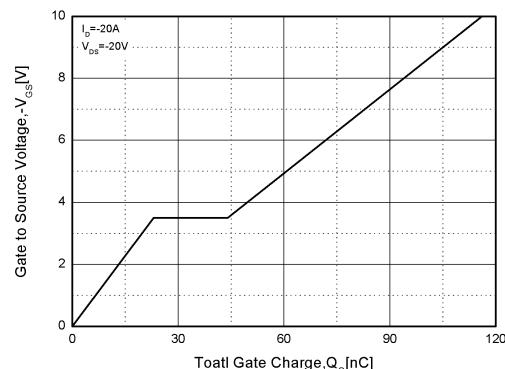


Figure6. Gate Charge

TYPICAL PERFORMANCE CHARACTERISTICS (cont.)

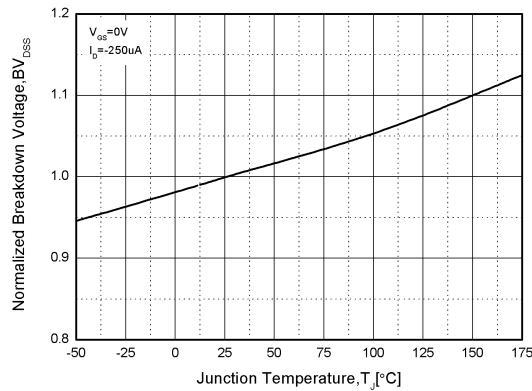


Figure 7. Normalized Breakdown Voltage vs. Temperature

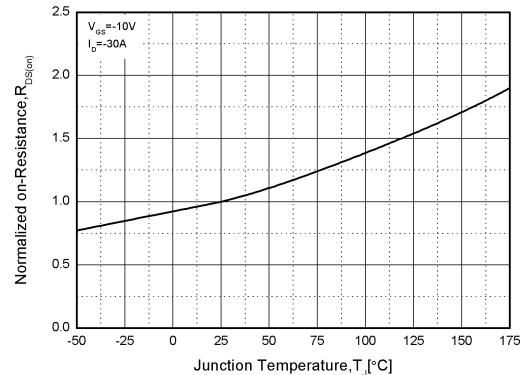
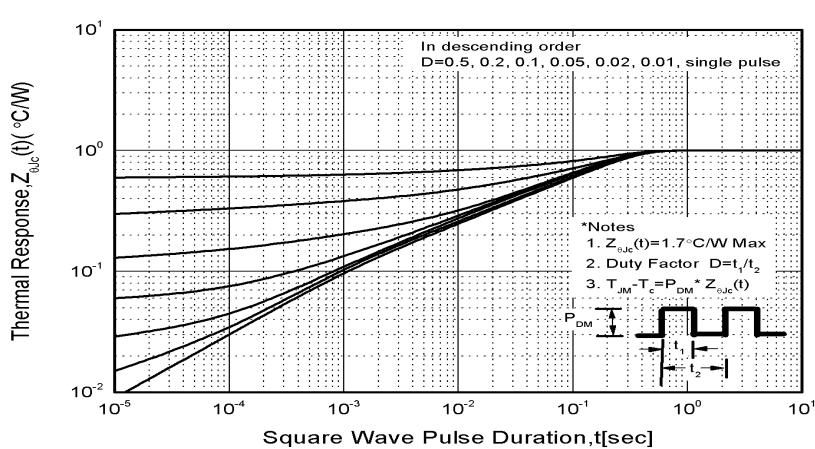
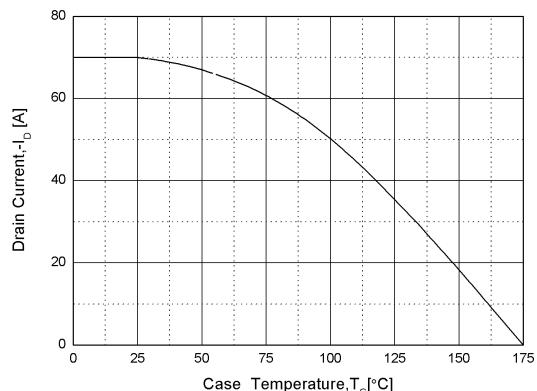
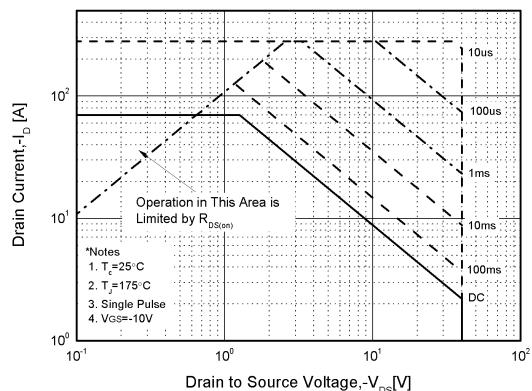
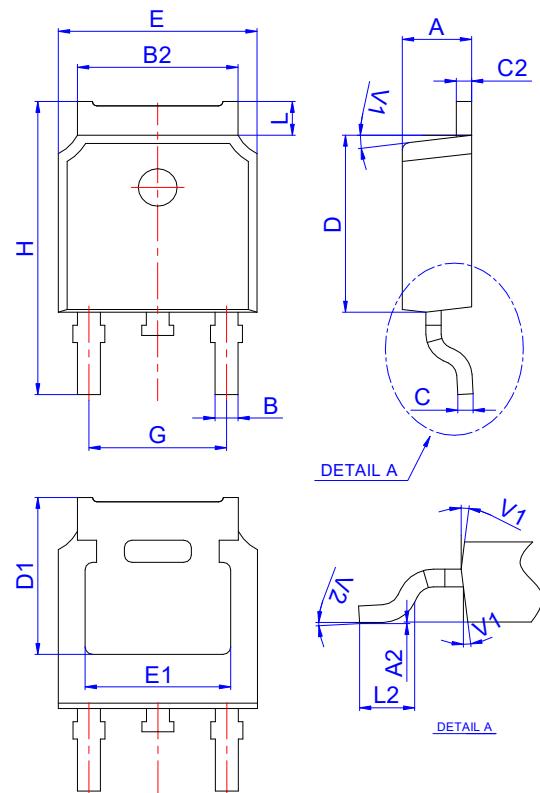


Figure 8. Normalized on Resistance vs. Temperature



TO-252-2L PACKAGE OUTLINE DRAWING



Symbols	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°